Abstracts

Full wave analysis of isolated pockets to improve isolation performances in silicon based technology

D. Bajon, S. Wane, H. Baudrand and P. Gamand. "Full wave analysis of isolated pockets to improve isolation performances in silicon based technology." 2002 MTT-S International Microwave Symposium Digest 02.2 (2002 Vol. II [MWSYM]): 987-990 vol.2.

This paper presents a versatile full wave analysis tool in which isolation pockets in IC's are readily introduced to perform intensive EM simulation including efficient introduction of via interconnects through metal levels. The obtained results are favorably compared to recent experimental published results.

❑ Return to main document.

Click on title for a complete paper.